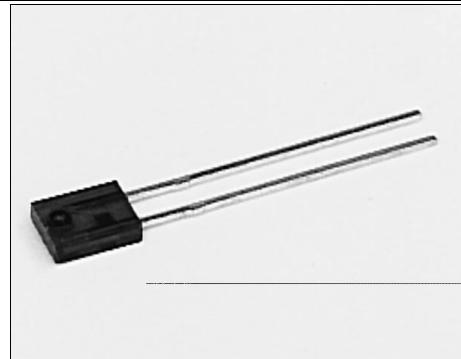


SEP8506

GaAs Infrared Emitting Diode

FEATURES

- Side-emitting plastic package
- 50° (nominal) beam angle
- 935 nm wavelength
- Mechanically and spectrally matched to SDP8406 phototransistor, SDP8106 photodarlington and SDP8000/8600 series Schmitt trigger



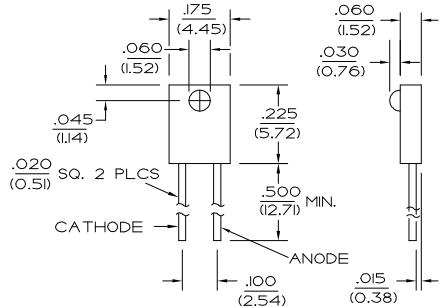
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DESCRIPTION

The SEP8506 is a gallium arsenide infrared emitting diode molded in a side-emitting red plastic package. The chip is positioned to emit radiation through a plastic lens from the side of the package.

OUTLINE DIMENSIONS in inches (mm)

Tolerance 3 plc decimals $\pm 0.005(0.12)$
 2 plc decimals $\pm 0.020(0.51)$



DIM_071.ds4

SEP8506

GaAs Infrared Emitting Diode

ELECTRICAL CHARACTERISTICS (25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Irradiance ⁽¹⁾ SEP8506-001 SEP8506-002 SEP8506-003	H	0.05 0.33 0.45	0.36 0.52 0.90		mW/cm ²	I _F =20 mA
Forward Voltage	V _F		1.5		V	I _F =20 mA
Reverse Breakdown Voltage	V _{BR}	3.0			V	I _R =10 µA
Peak Output Wavelength	λ _p	935			nm	
Spectral Bandwidth	Δλ	50			nm	
Spectral Shift With Temperature	Δλ _p /ΔT	0.3			nm/°C	
Beam Angle ⁽²⁾	Ø	50			degr.	I _F =Constant
Radiation Rise And Fall Time	t _r , t _f	0.7			µs	

Notes

1. Measured in mW/cm² into a 0.104 (2.64) diameter aperture placed 0.535 (13.6) from the lens tip.
2. Beam angle is defined as the total included angle between the half intensity points.

ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Continuous Forward Current	50 mA
Power Dissipation	100 mW ⁽¹⁾
Storage Temperature Range	-40°C to 85°C
Operating Temperature Range	-40°C to 85°C
Soldering Temperature (5 sec)	240°C

Notes

1. Derate linearly from 25°C free-air temperature at the rate of 0.78 mW/°C.

SCHEMATIC



Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

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SEP8506

GaAs Infrared Emitting Diode

Fig. 1 Radiant Intensity vs
Angular Displacement

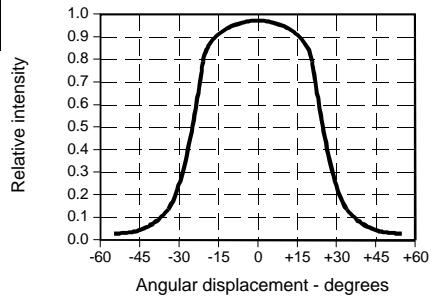


Fig. 3 Forward Voltage vs
Forward Current

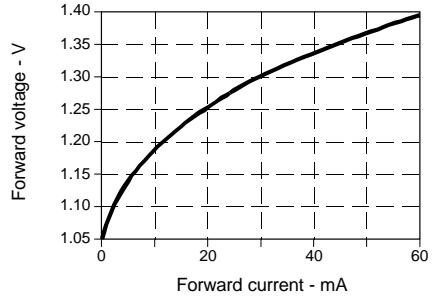


Fig. 5 Spectral Bandwidth

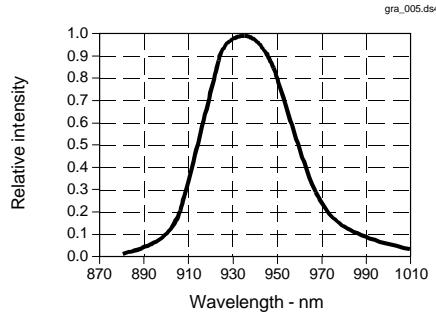


Fig. 2 Radiant Intensity vs
Forward Current

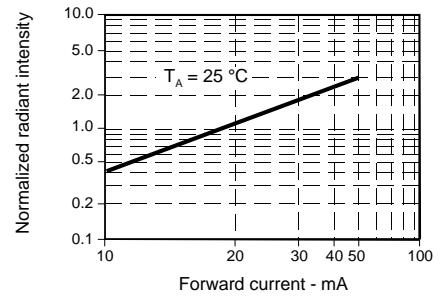


Fig. 4 Forward Voltage vs
Temperature

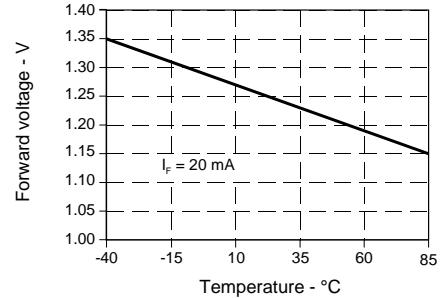
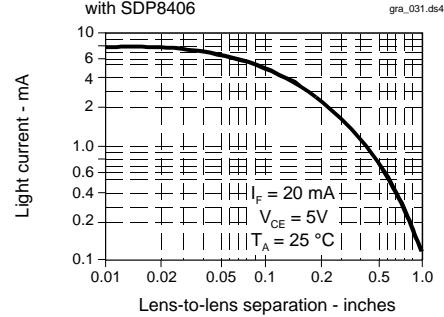
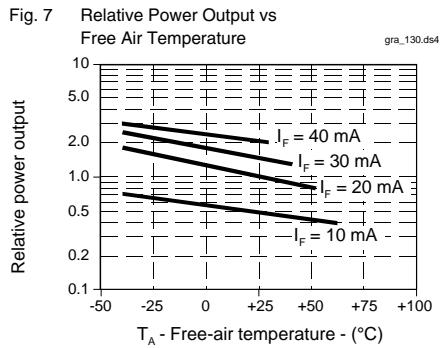


Fig. 6 Coupling Characteristics
with SDP8406



SEP8506

GaAs Infrared Emitting Diode



All Performance Curves Show Typical Values

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